National Semiconductor

LM6165/LM6265/LM6365 High Speed Operational Amplifier

General Description

The LM6165 family of high-speed amplifiers exhibits an excellent speed-power product in delivering 300 V/µs and 725 MHz GBW (stable for gains as low as +25) with only 5 mA of supply current. Further power savings and application convenience are possible by taking advantage of the wide dynamic range in operating supply voltage which extends all the way down to +5V.

These amplifiers are built with National's VIP[™] (Vertically Integrated PNP) process which produces fast PNP transistors that are true complements to the already fast NPN devices. This advanced junction-isolated process delivers high speed performance without the need for complex and expensive dielectric isolation.

Features

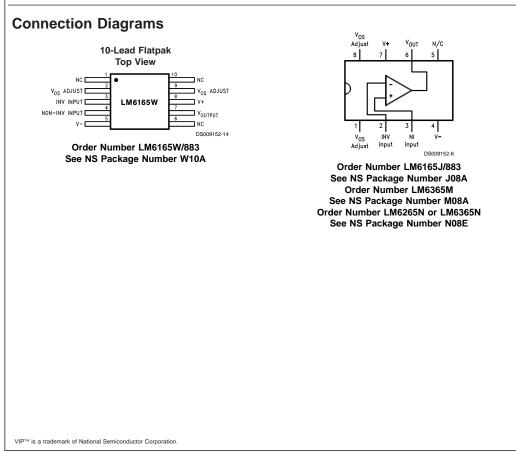
■ High slew rate: 300 V/µs

- High GBW product: 725 MHz
- Low supply current: 5 mA
- Fast settling: 80 ns to 0.1%
- Low differential gain: <0.1%
- Low differential phase: <0.1°
- Wide supply range: 4.75V to 32V
- Stable with unlimited capacitive load

Applications

Video amplifier

- Wide-bandwidth signal conditioning
- Radar
- Sonar



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May 1999

	Temperature Range			NSC
Military	Industrial	Commercial		Drawing
–55°C ≤ T_A ≤ +125°C	–25°C ≤ T_A ≤ +85°C	$0^{\circ}C \leq T_{A} \leq +70^{\circ}C$		
	LM6265N	LM6365N	8-Pin	N08E
			Molded DIP	
LM6165J/883			8-Pin	J08A
5962-8962501PA			Ceramic DIP	
		LM6365M	8-Pin Molded	M08A
			Surface Mt.	
LM6165WG/883			10-Lead	WG10A
5962-8962501XA			Ceramic SOIC	
LM6165W883			10-Pin	W10A
5962-8962501HA			Ceramic Flatpak	

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications. See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices. Storage Temp Range Max Junction Temperature

Supply Voltage (V ⁺ – V ⁻)	36V
Differential Input Voltage	
(Note 7)	±8V
Common-Mode Voltage	
Range (Note 11)	$(V^+ - 0.7V)$ to $(V^- + 0.7V)$
Output Short Circuit to GND	
(Note 2)	Continuous
Soldering Information	
Dual-In-Line Package (N, J)	
Soldering (10 sec.)	260°C
Small Outline Package (M)	0450
Vapor Phase (60 sec.) Infrared (15 sec.)	215°C 220°C
initaleu (13 Sec.)	220 0

-65°C to +150°C 150°C ESD Tolerance (Notes 7, 8) ±700V

Operating Ratings

(Note 3)

Temperature Range (Note 3)	
LM6165, LM6165J/883	$-55^{\circ}C \le T_{J} \le +125^{\circ}C$
LM6265	$-25^{\circ}C \le T_{J} \le +85^{\circ}C$
LM6365	$0^{\circ}C \le T_{J} \le +70^{\circ}C$
Supply Voltage Range	4.75V to 32V

DC Electrical Characteristics

The following specifications apply for $T_A = T_J = T$	Supply Voltage = $\pm 15V$, V _{CM} = 0 T _{MIN} to T _{MAX} ; all other limits T _A =), R _L ≥ 100 kΩ and F T _J = 25°C.	$R_s = 50\Omega$ unless of	otherwise noted.

Symbol	Parameter	Conditions	Тур	LM6165	LM6265	LM6365	Units
				Limit	Limit	Limit	1
				(Notes 4, 12)	(Note 4)	(Note 4)	
Vos	Input Offset Voltage		1	3	3	6	mV
				4	4	7	Max
Vos	Input Offset Voltage		3				µV/°C
Drift	Average Drift						
l _b	Input Bias Current		2.5	3	3	5	μA
				6	5	6	Max
l _{os}	Input Offset Current		150	350	350	1500	nA
				800	600	1900	Max
l _{os}	Input Offset Current		0.3				nA/°C
Drift	Average Drift						
R _{IN}	Input Resistance	Differential	20				kΩ
C _{IN}	Input Capacitance		6.0				pF
A _{VOL}	Large Signal	$V_{OUT} = \pm 10V,$	10.5	7.5	7.5	5.5	V/m\
	Voltage Gain	$R_L = 2 k\Omega$		5.0	6.0	5.0	Min
	(Note 10)	$R_L = 10 \ k\Omega$	38				1
V _{CM}	Input Common-Mode	Supply = $\pm 15V$	+14.0	+13.9	+13.9	+13.8	V
	Voltage Range			+13.8	+13.8	+13.7	Min
			-13.6	-13.4	-13.4	-13.3	V
				-13.2	-13.2	-13.2	Min
		Supply = +5V	4.0	3.9	3.9	3.8	V
		(Note 5)		3.8	3.8	3.7	Min
			1.4	1.6	1.6	1.7	V
				1.8	1.8	1.8	Max
CMRR	Common-Mode	$-10V \le V_{CM} \le +10V$	102	88	88	80	dB
	Rejection Ratio			82	84	78	Min
PSRR	Power Supply	$\pm 10V \le V^{\pm} \le \pm 16V$	104	88	88	80	dB
	Rejection Ratio			82	84	78	Min

	ce limits apply for $I_A = I$	ly for Supply Voltage = ± 13 J = T _{MIN} to T _{MAX} ; all other	limits $T_A =$	Т _Ј = 25°С.	0		
Symbol	Parameter	Conditions	Тур	LM6165 Limit (Notes 4, 12)	LM6265 Limit (Note 4)	LM6365 Limit (Note 4)	Units
Vo	Output Voltage	Supply = $\pm 15V$,	+14.2	+13.5	+13.5	+13.4	V
	Swing	$R_{L} = 2 k\Omega$		+13.3	+13.3	+13.3	Min
			-13.4	-13.0	-13.0	-12.9	V
				-12.7	-12.8	-12.8	Min
		Supply = +5V	4.2	3.5	3.5	3.4	V
		$R_{L} = 2 k\Omega$ (Note 5)		3.3	3.3	3.3	Min
			1.3	1.7	1.7	1.8	V
				2.0	1.9	1.9	Max
	Output Short	Source	65	30	30	30	mA
	Circuit Current			20	25	25	Min
		Sink	65	30	30	30	mA
				20	25	25	Min
I _s	Supply Current		5.0	6.5	6.5	6.8	mA
				6.8	6.7	6.9	Max

AC Electrical Characteristics

.

The following specifications apply for Supply Voltage = $\pm 15V$, $V_{CM} = 0$, $R_L \ge 100 \text{ k}\Omega$ and $R_S = 50\Omega$ unless otherwise noted. Boldface limits apply for $T_A = T_J = T_{MIN}$ to T_{MAX} ; all other limits $T_A = T_J = 25^{\circ}C$. (Note 6)

Symbol	Parameter	Conditions	Тур	LM6165	LM6265	LM6365	Units
				Limit	Limit	Limit	1
				(Notes 4, 12)	(Note 4)	(Note 4)	
GBW	Gain Bandwidth	F = 20 MHz	725	575	575	500	MHz
				350			Min
	Product	Supply = $\pm 5V$	500				1
SR	Slew Rate	A _V = +25 (Note 9)	300	200	200	200	V/µs
				180			Min
		Supply = $\pm 5V$	200				1
PBW	Power Bandwidth	V _{OUT} = 20 V _{PP}	4.5				MHz
	Product						
ts	Settling Time	10V Step to 0.1%	80				ns
		$A_V = -25$, $R_L = 2 k\Omega$					
φ _m	Phase Margin	A _V = +25	45				Deg
A _D	Differential Gain	NTSC, $A_V = +25$	<0.1				%
φ _D	Differential Phase	NTSC, $A_V = +25$	<0.1				Deg
e _{np-p}	Input Noise Voltage	F = 10 kHz	5				nV/√Hz
i _{np-p}	Input Noise Current	F = 10 kHz	1.5				pA/√Hz

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

Note 2: Continuous short-circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.

Note 3: The typical junction-to-ambient thermal resistance of the molded plastic DIP (N) is 105°C/Watt, and the molded plastic SO (M) package is 155°C/Watt, and the cerdip (J) package is 125°C/Watt. All numbers apply for packages soldered directly into a printed circuit board.

Note 4: All limits guaranteed by testing or correlation.

Note 5: For single supply operation, the following conditions apply: V+ = 5V, V- = 0V, V_{CM} = 2.5C, V_{OUT} = 2.5V. Pin 1 & Pin 8 (V_{OS} Adjust) are each connected to Pin 4 (V-) to realize maximum output swing. This connection will degrade V_{OS} .

Note 6: $C_L \le 5 \text{ pF.}$

Note 7: In order to achieve optimum AC performance, the input stage was designed without protective clamps. Exeeding the maximum differential input voltage results in reverse breakdown of the base-emitter junction of one of the input transistors and probable degradation of the input parameters (especially V_{OS}, I_{OS}, and Noise).

AC Electrical Characteristics (Continued)

Note 8: The average voltage that the weakest pin combinations (those involving Pin 2 or Pin 3) can withstand and still conform to the datasheet limits. The test circuit used consists of the human body model of 100 pF in series with 1500Ω.

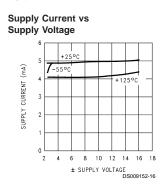
Note 9: V_{IN} = 0.8V step. For supply = ±5V, V_{IN} = 0.2V step.

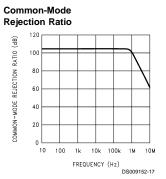
Note 10: Voltage Gain is the total output swing (20V) divided by the input signal required to produce that swing.

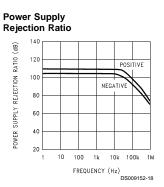
Note 11: The voltage between V⁺ and either input pin must not exceed 36V.

Note 12: A military RETS electrical test specification is available on request. At the time of printing, the LM6165J/883 RETS spec complied with the Boldface limits in this column. The LM6165J/883 may also be procured as Standard Military Drawing #5962-8962501PA.

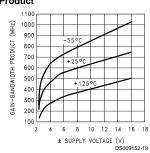
Typical Performance Characteristics $R_L = 10 \text{ k}\Omega$, $T_A = 25^{\circ}C$ unless otherwise specified



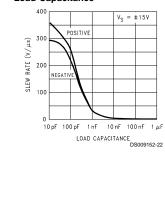




Gain-Bandwidth Product



Slew Rate vs Load Capacitance



Propagation Delay, **Rise and Fall Times**

Overshoot vs

30

25

15

10

0

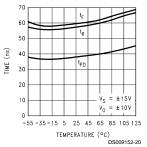
10 pF

100 pF

1 nF

OVERSHOOT (%) 20

Capacitive Load

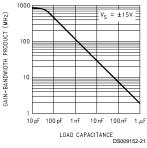


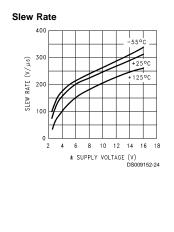
 $V_S = \pm 15V$

 $A_V = +25$ $R_F = 2 k \Omega$

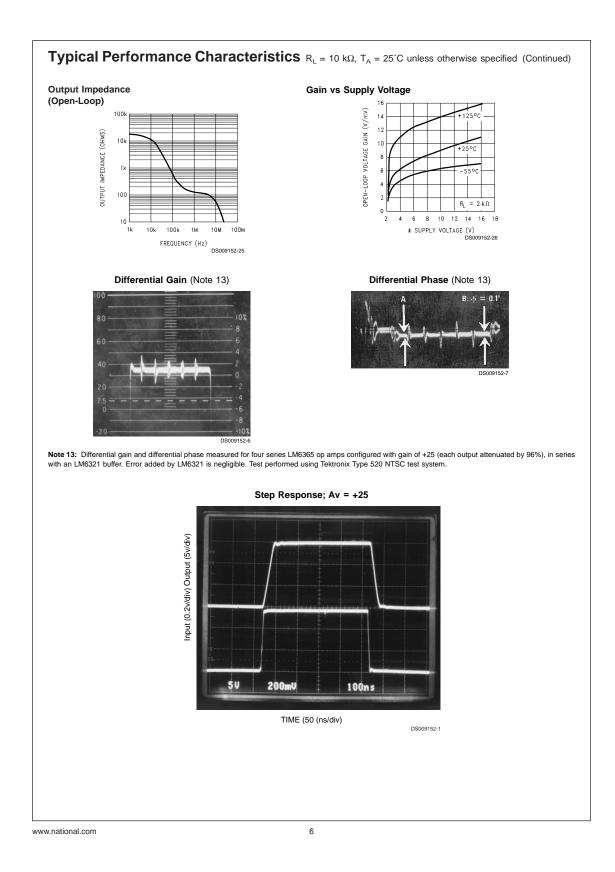
10 nF 100 nF DS009152-23

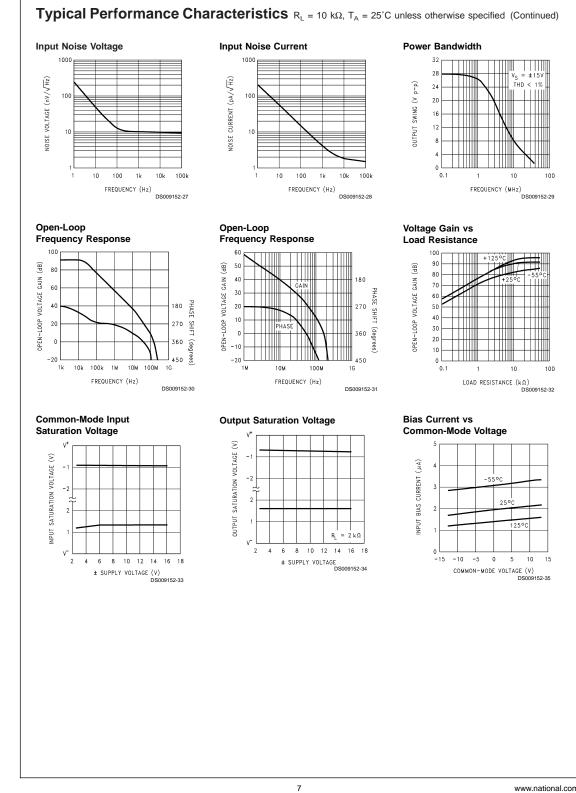
Gain-Bandwidth Product vs Load Capacitance



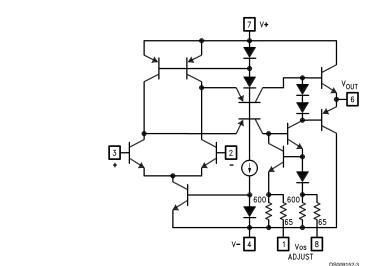


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Simplified Schematic



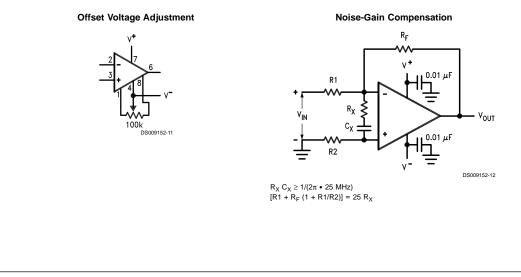
The LM6365 is stable for gains of 25 or greater. The LM6361 and LM6364, specified in separate datasheets, are compensated versions of the LM6365. The LM6361 is unity-gain stable, while the LM6364 is stable for gains as low as 5. The LM6361, and LM6364 have the same high slew rate as the LM6365, typically 300 V/ μ s.

To use the LM6365 for gains less than 25, a series resistor-capacitor network should be added between the input pins (as shown in the Typical Applications, Noise Gain Compensation) so that the high-frequency noise gain rises to at least 25.

Power supply bypassing will improve stability and transient response of the LM6365, and is recommended for every design. 0.01 μF to 0.1 μF ceramic capacitors should be used



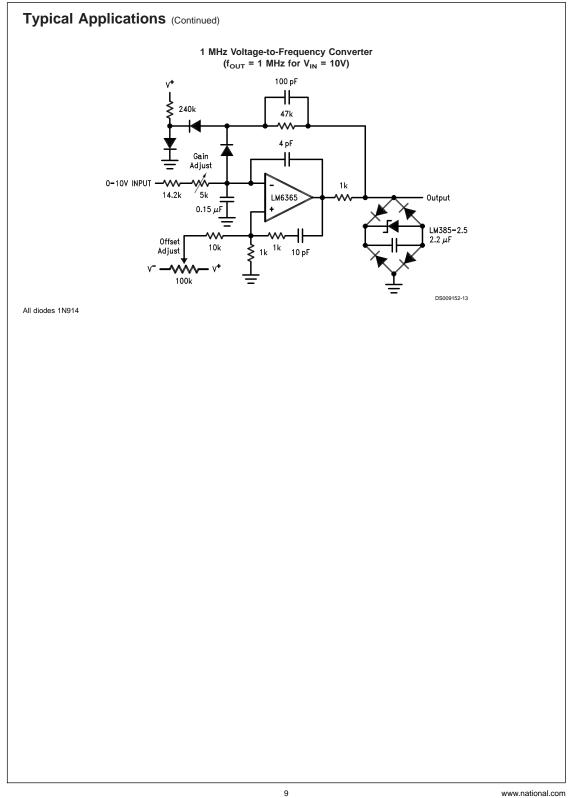
Application Tips

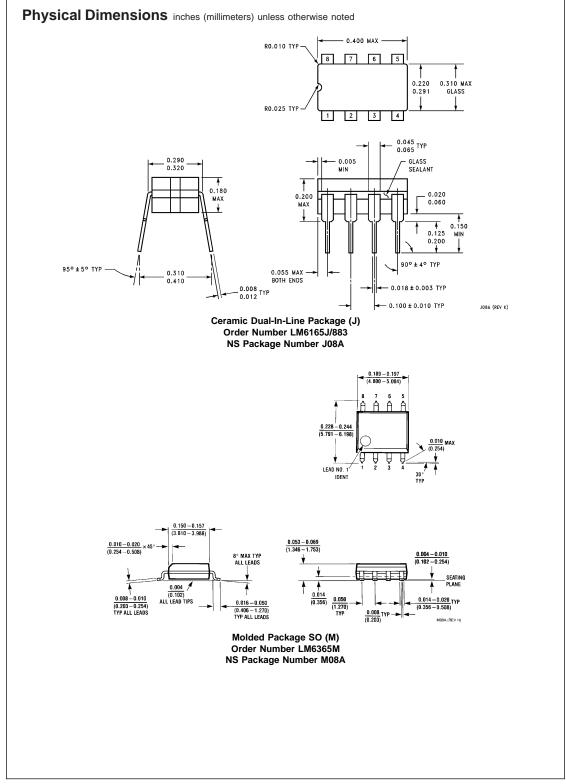


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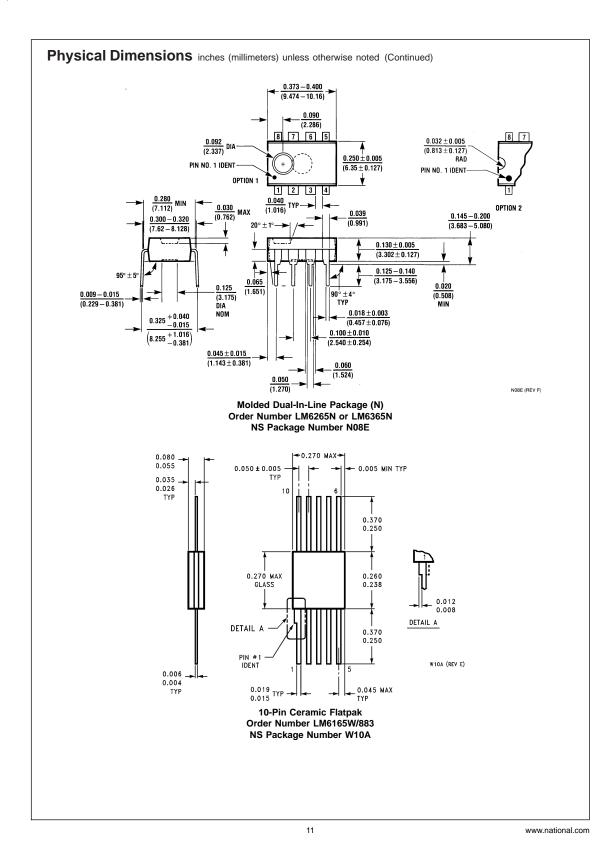
(from each supply "rail" to ground); an additional 2.2 μF to 10 μF (tantalum) may be required for extra noise reduction. Keep all leads short to reduce stray capacitance and lead inductance, and make sure ground paths are low-impedance, especially where heavier currents will be flowing. Stray capacitance in the circuit layout can cause signal coupling between adjacent nodes, and can cause circuit gain to unintentionally vary with frequency.

Breadboarded circuits will work best if they are built using generic PC boards with a good ground plane. If the op amps are used with sockets, as opposed to being soldered into the circuit, the additional input capacitance may degrade circuit performance.





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Notes

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